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Nonactivated adsorption of CH_3Cl on $\text{Si}(100)\text{-}2\times 1$ studied by LEED, AES and semiempirical method.

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The adsorption processes of methyl chloride on $\text{Si}(100)\text{-}2\times 1$ have been studied by low energy electron diffraction (LEED), Auger electron spectroscopy (AES) and semiempirical PM3 calculations. The dissociative adsorption of the methyl chloride on $\text{Si}(100)$ takes place without breaking of the silicon dimer with high efficiency. For adsorption at the room temperature, the existence of a precursor state is confirmed by the behavior of the sticking probability depending on the coverage and temperature. From AES measurements, the determined activation barrier of adsorption (ΔH_{ads}) is -28.4 kJ/mol. This results indicate that the dissociative process is nonactivated. The optimized precursor state of CH_3Cl on the $\text{Si}(100)\text{-}2\times 1$ surface was determined by PM3 calculations based on a cluster model.